

SEMITRANSTM M1

Power MOSFET Modules

SKM 180A020

Features

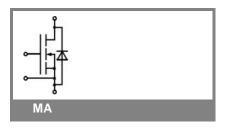
- N Channel, enhancement mode
- Avalanche characteristics
- Short internal connections avoid oscillations
- Isolated copper baseplates
- All electrical connections on top for easy busbaring
- Large clearance (10mm) and creepage distances (13mm)
- UL recognized, file no. E 63 532

Typical Applications*

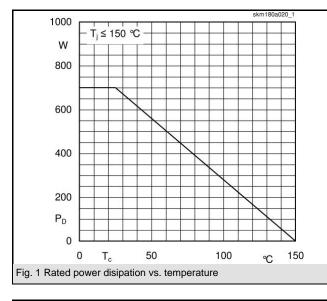
- Switched mode power supplies
- DC servo and robot drives
- DC choppers
- UPS equipment
- Plasma cutting
- Not suitable for linear amplification

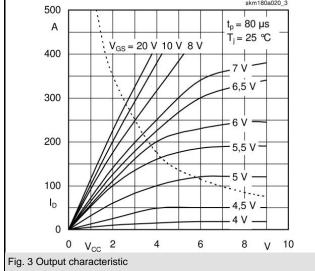
Absolute Maximum Ratings		T_c = 25 °C, unless otherwise specified					
Symbol	Conditions	Values	Units				
V _{DS}		200	V				
I _D	T _s = 25 (80) °C	180 (135)	А				
I _{DM}	1 ms	540	Α				
V _{GS}		± 20	V				
V _{GS} T _{vj} , (T _{stg})		- 40 + 150 (125)	°C				
V _{isol}	AC, 1 min.	2500	V				
Inverse diode							
I _F = - I _S		180	А				
$I_{FM} = -I_{SM}$		540	А				

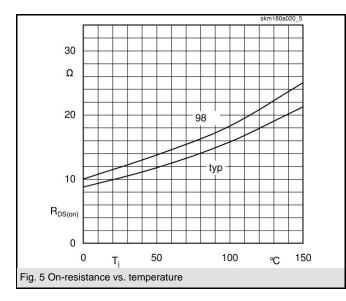
Characteristics		T _c = 25	T _c = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units	
V _{(BR)DSS}	V _{GS} = 0 V, I _D = 0,25 mA	200			V	
V _{GS(th)}	$V_{GS} = V_{DS}, I_D = 1 \text{ mA}$	2,1	3	4	V	
I _{DSS}	V _{GS} = 0 V, V _{DS} = 200 V, T _i = 25 (125) °C		50 (300)	250 (1000)	μA	
I _{GSS}	$V_{GS} = 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$		10	100	nA	
R _{DS(on)}	V _{GS} = 10 V, I _D = 110 A		9	11	mΩ	
9 _{fs}	V _{DS} = 25 V, I _D = 110 A	80	100		S	
C _{CHC}	V _{GS} = 0, V _{DS} = 25 V, f = 1 MHz			160	pF	
C _{iss}			16	24	nF	
C _{oss}			3	4,5	nF	
C _{rss}			1,5	2	nF	
L _{DS}				20	nH	
t _{d(on)}	V _{DD} = 100 V, I _D = 80 A,		100		ns	
t _r `´	V_{GS} = = 10 V, R_{G} = 3,3 Ω		200		ns	
t _{d(off)}			900		ns	
t _f			220		ns	
Inverse d	iode	•			•	
V _{SD}	I _F = 360 A; V _{GS} = 0 V		1,3	1,5	V	
t _{rr}	T _j = 25 (125) °C		0,5		ns	
Q _{rr}	T _j = 25 °C		10 (12)		μC	
I _{rr}	T _j = °C				А	
Thermal of	characteristics	•			•	
R _{th(j-c)}	per MOSFET			0,18	K/W	
R _{th(c-s)}	M_s , surface 10 μ m, per module			0,05	K/W	
Mechanic	al data					
M _s	to heatsink (M6)	4		5	Nm	
Mť	for terminals (M5)				Nm	
w				130	g	

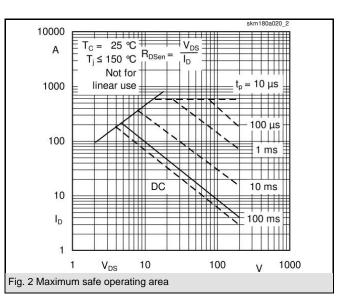


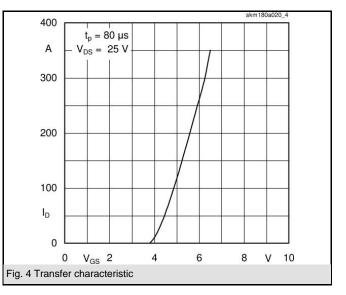
03-12-2008 NOS

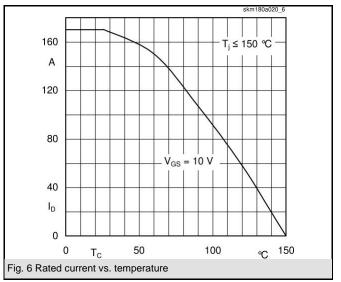




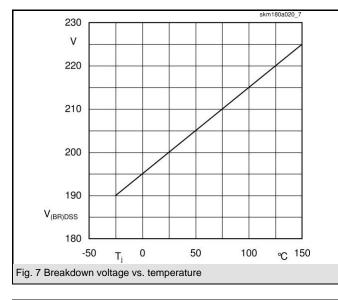


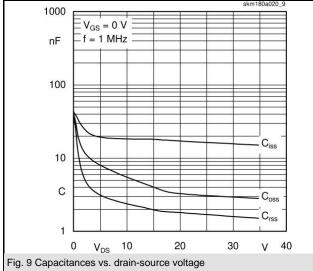


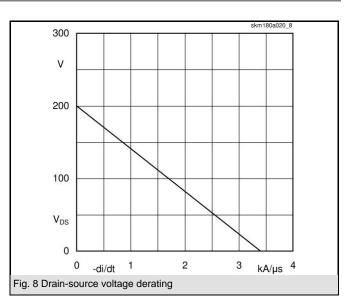


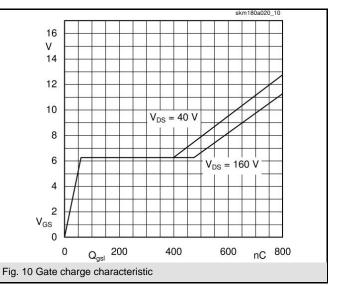


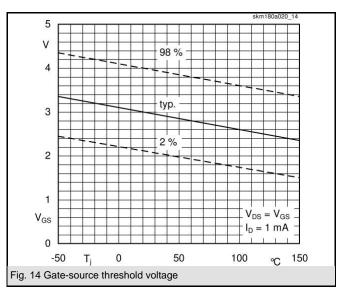
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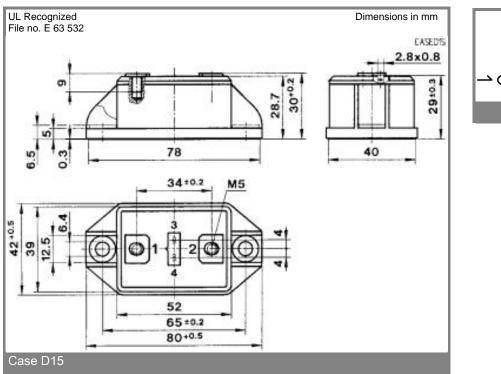


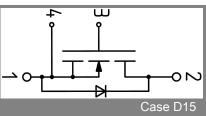






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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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